NSN 5961-01-058-7804

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-058-7804 **Inclosure Material:** Metal **Overall Length:** Between 0.293 inches and 0.357 inches **Terminal Length:** Between 1.000 inches and 1.625 inches **Overall Diameter:** Between 0.215 inches and 0.235 inches **Function For Which Designed:** Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 18.0 breakdown voltage, dc and 15.3 working peak reverse voltage **Voltage Tolerance In Percent:** -5.0/+5.0 **Maximum Operating Tempurature Per Measurement Point:**

175.0 degrees celsius ambient air

Special Features:

1.0w rated average power dissipation; 1500w repetetive peak pulse power.

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 uninsulated wire lead

Specification Data:

81349-mil-s-19500/500 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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